

MOSFET – Power, Single N-Channel, STD Gate, DUAL COOL[®] DFN8 5x6

80 V, 2.6 mΩ, 154 A

NTMFSC2D6N08X

Features

- Advanced Dual-Sided Cooled Packaging
- Low Q_{RR} , Soft Recovery Body Diode
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- Synchronous Rectification (SR) in DC-DC and AC-DC
- Primary Switch in Isolated DC-DC Converter
- Motor Drives

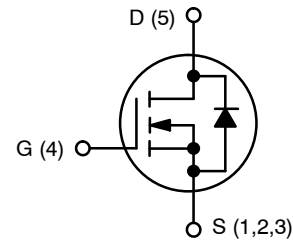
MAXIMUM RATINGS ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise stated)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		V_{DSS}	80	V
Gate-to-Source Voltage		V_{GS}	±20	V
Continuous Drain Current (Note 1)	$T_C = 25\text{ }^{\circ}\text{C}$	I_D	154	A
	$T_C = 100\text{ }^{\circ}\text{C}$		109	
Power Dissipation (Note 1)	$T_C = 25\text{ }^{\circ}\text{C}$	P_D	133	W
Pulsed Drain Current	$T_C = 25\text{ }^{\circ}\text{C}$, $t_p = 100\text{ }\mu\text{s}$	I_{DM}	634	A
Pulsed Source Current (Body Diode)		I_{SM}	634	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	−55 to +175	$^{\circ}\text{C}$
Source Current (Body Diode)		I_S	201	A
Single Pulse Avalanche Energy ($I_{PK} = 53\text{ A}$) (Note 3)		E_{AS}	140	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^{\circ}\text{C}$

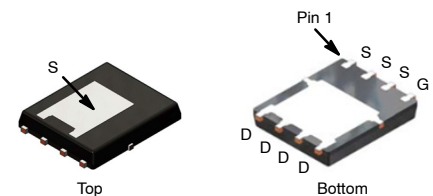
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
- Actual continuous current will be limited by thermal & electromechanical application board design.
- E_{AS} of 140 mJ is based on started $T_J = 25\text{ }^{\circ}\text{C}$, $I_{AS} = 53\text{ A}$, $V_{DD} = 64\text{ V}$, $V_{GS} = 10\text{ V}$, 100% avalanche tested

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
80 V	2.6 mΩ @ 10 V	154 A

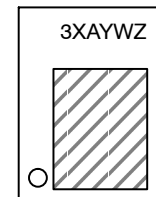


N-CHANNEL MOSFET



DFN8 5x6.15
DUAL COOL 56
CASE 506EG

MARKING DIAGRAM



- 3X = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
Z = Assembly Lot Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

THERMAL CHARACTERISTICS

Parameter	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case, Bottom	$R_{\theta JC}$	1.12	$^{\circ}\text{C/W}$
Thermal Resistance, Junction-to-Case, Top	$R_{\theta JC}$	1.7	$^{\circ}\text{C/W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	39	$^{\circ}\text{C/W}$

4. Surface-mounted on FR4 board using 1 in² pad, 1 oz. Cu.
 5. $R_{\theta JA}$ is determined by the user's board design.

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	80			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$\Delta V_{(BR)DSS} / \Delta T_J$	$I_D = 1\text{ mA}$. Referenced to 25°C		31.6		$\text{mV}/^{\circ}\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 80\text{ V}, T_J = 25^{\circ}\text{C}$			10	μA
		$V_{DS} = 80\text{ V}, T_J = 125^{\circ}\text{C}$			250	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$			100	nA

ON CHARACTERISTICS

Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 37\text{ A}$		2.2	2.6	$\text{m}\Omega$
		$V_{GS} = 6\text{ V}, I_D = 18\text{ A}$		3.3	5.2	
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 184\text{ }\mu\text{A}$	2.4		3.6	V
Gate Threshold Voltage Temperature Coefficient	$\Delta V_{GS(TH)} / \Delta T_J$	$V_{GS} = V_{DS}, I_D = 184\text{ }\mu\text{A}$		-7.5		$\text{mV}/^{\circ}\text{C}$
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{ V}, I_D = 37\text{ A}$		115		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance*	C_{ISS}	$V_{GS} = 0\text{ V}, V_{DS} = 40\text{ V}, f = 1\text{ MHz}$	1600	3200	4800	pF
Output Capacitance*	C_{OSS}			930	1400	
Reverse Transfer Capacitance*	C_{RSS}			14	26	
Output Charge	Q_{OSS}			66		
Total Gate Charge*	$Q_{G(TOT)}$	$V_{GS} = 6\text{ V}, V_{DD} = 40\text{ V}, I_D = 37\text{ A}$		28		nC
		$V_{GS} = 10\text{ V}, V_{DD} = 40\text{ V}, I_D = 37\text{ A}$		45	68	
Threshold Gate Charge	$Q_{G(TH)}$	$V_{GS} = 10\text{ V}, V_{DD} = 40\text{ V}, I_D = 37\text{ A}$		10		
Gate-to-Source Charge	Q_{GS}			15		
Gate-to-Drain Charge*	Q_{GD}			7	13	
Gate Plateau Voltage	V_{GP}			4.7		V
Gate Resistance*	R_G	$f = 1\text{ MHz}$	0.4	0.8	1.2	Ω

SWITCHING CHARACTERISTICS

Turn-On Delay Time	$t_{d(ON)}$	Resistive Load, $V_{GS} = 0/10\text{ V}, V_{DD} = 40\text{ V},$ $I_D = 37\text{ A}, R_G = 2.5\text{ }\Omega$		24		ns
Rise Time	t_r			8		
Turn-Off Delay Time	$t_{d(OFF)}$			35		
Fall Time	t_f			6		



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ELECTRICAL CHARACTERISTICS ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified) (continued)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
SOURCE-TO-DRAIN DIODE CHARACTERISTICS						
Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 37\text{ A}, T_J = 25\text{ }^{\circ}\text{C}$		0.82	1.2	V
		$V_{GS} = 0\text{ V}, I_S = 37\text{ A}, T_J = 125\text{ }^{\circ}\text{C}$		0.66		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI/dt = 1000\text{ A}/\mu\text{s},$ $I_S = 37\text{ A}, V_{DD} = 40\text{ V}$		23		ns
Charge Time	t_a			13		
Discharge Time	t_b			11		
Reverse Recovery Charge	Q_{RR}			163		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

* Defined by design, not subject to production test.



TYPICAL CHARACTERISTICS

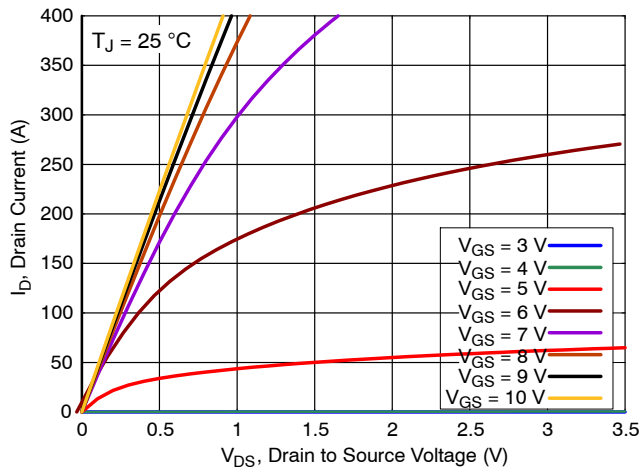


Figure 1. On-Region Characteristics

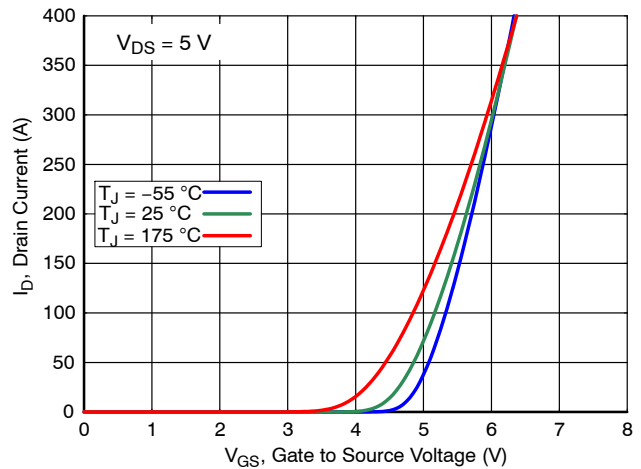


Figure 2. Transfer Characteristics

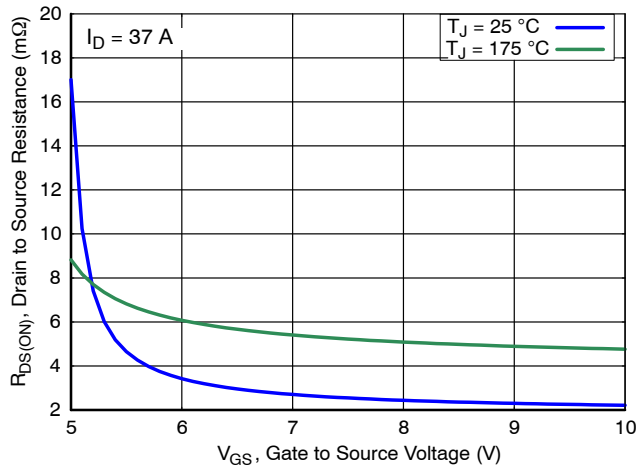


Figure 3. On-Resistance vs. Gate Voltage

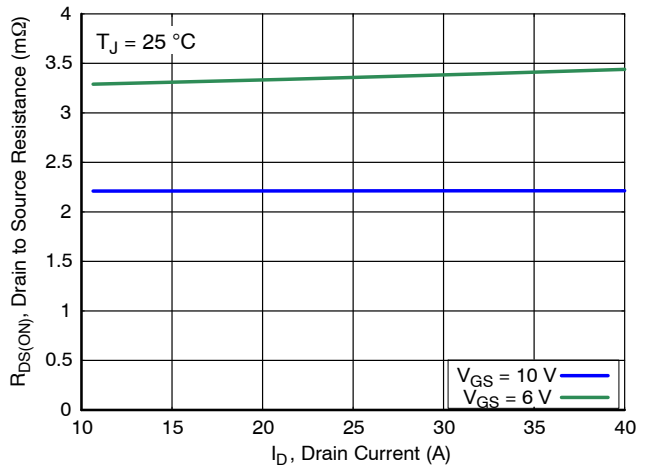


Figure 4. On-Resistance vs. Drain Current

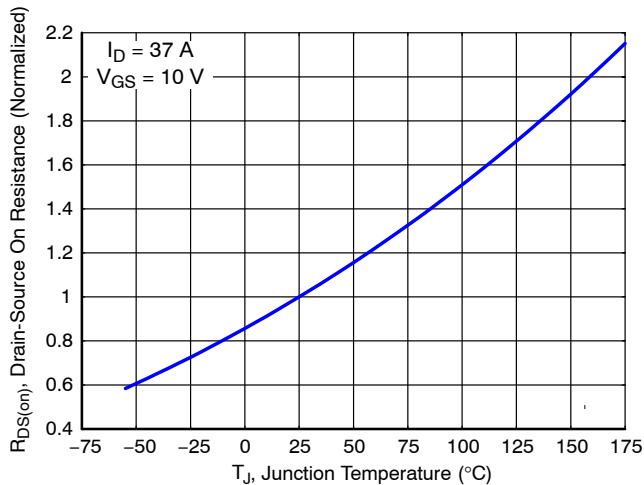


Figure 5. Normalized ON Resistance vs. Junction Temperature

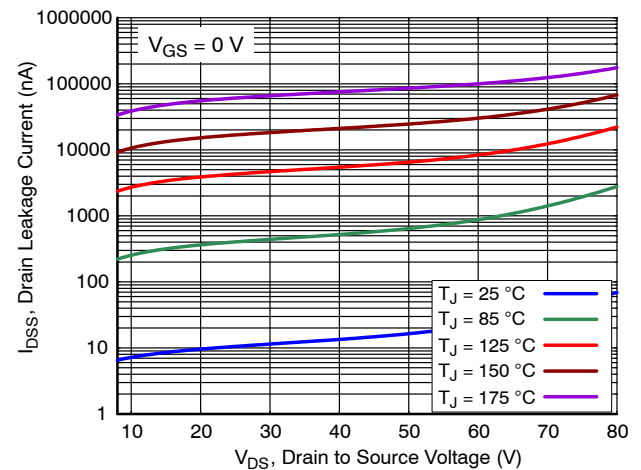


Figure 6. Drain Leakage Current vs. Drain Voltage

TYPICAL CHARACTERISTICS

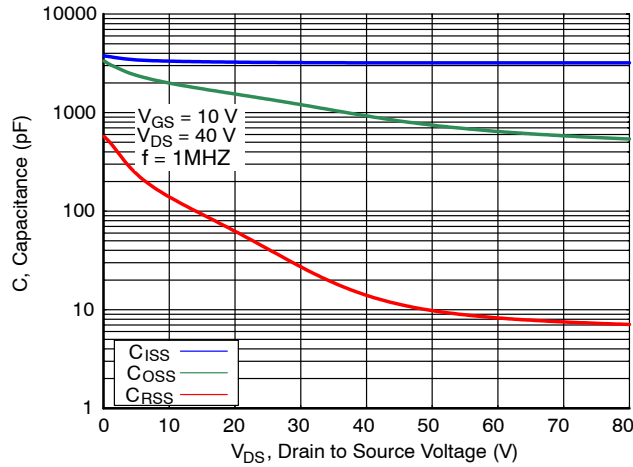


Figure 7. Capacitance Characteristics

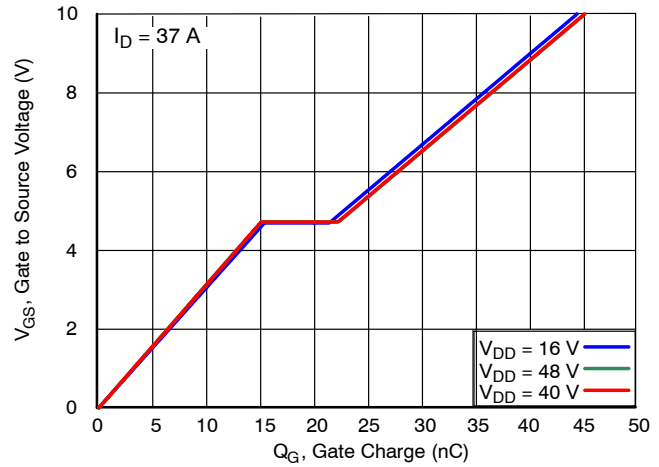


Figure 8. Gate Charge Characteristics

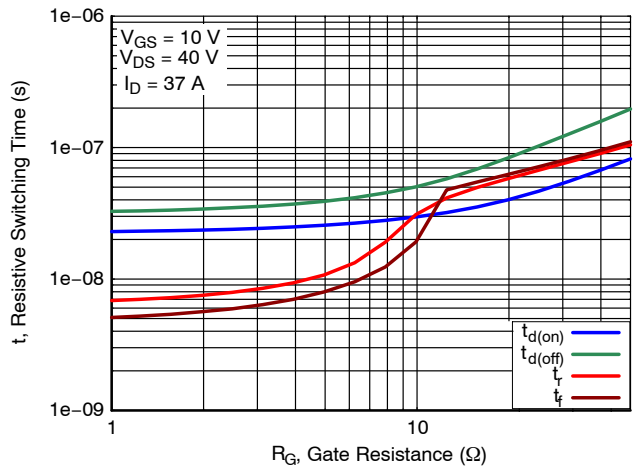


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

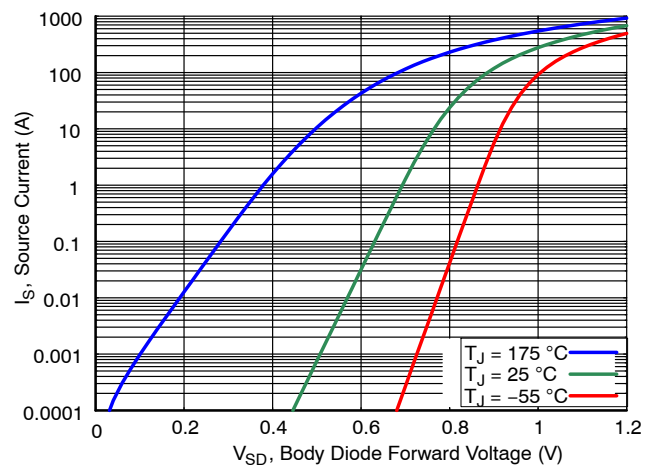


Figure 10. Diode Forward Characteristics

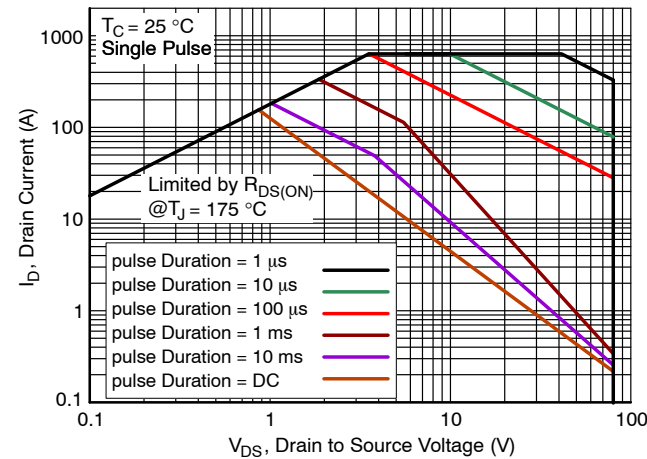


Figure 11. Safe Operating Area (SOA)

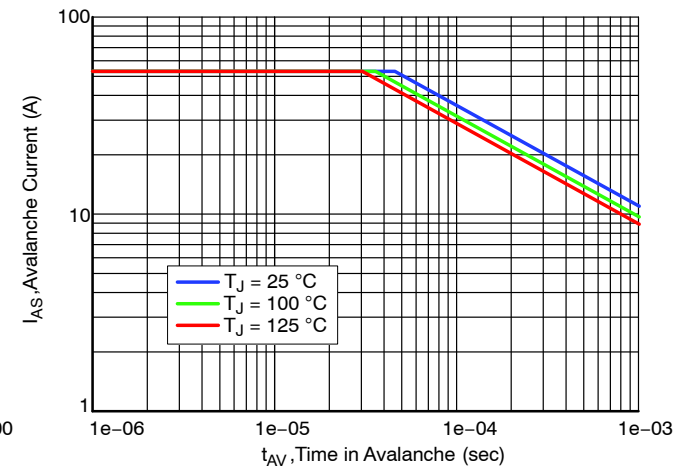


Figure 12. Avalanche Current vs. Pulse Time (UIS)

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TYPICAL CHARACTERISTICS

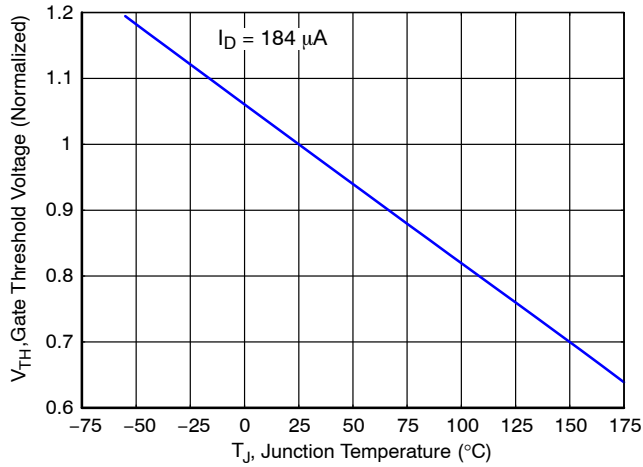


Figure 13. Gate Threshold Voltage vs. Junction Temperature

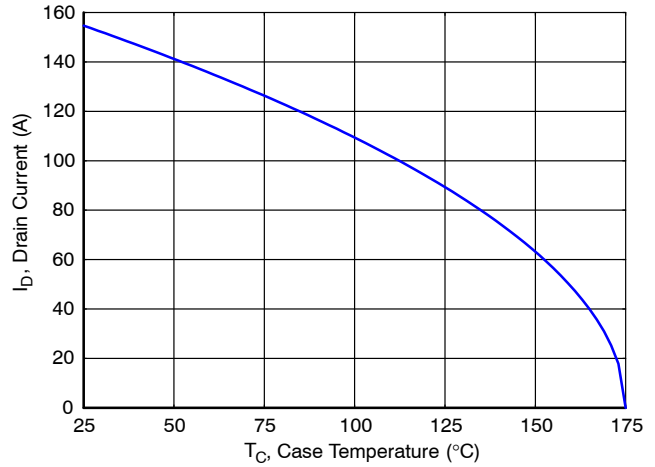


Figure 14. Maximum Current vs. Case Temperature

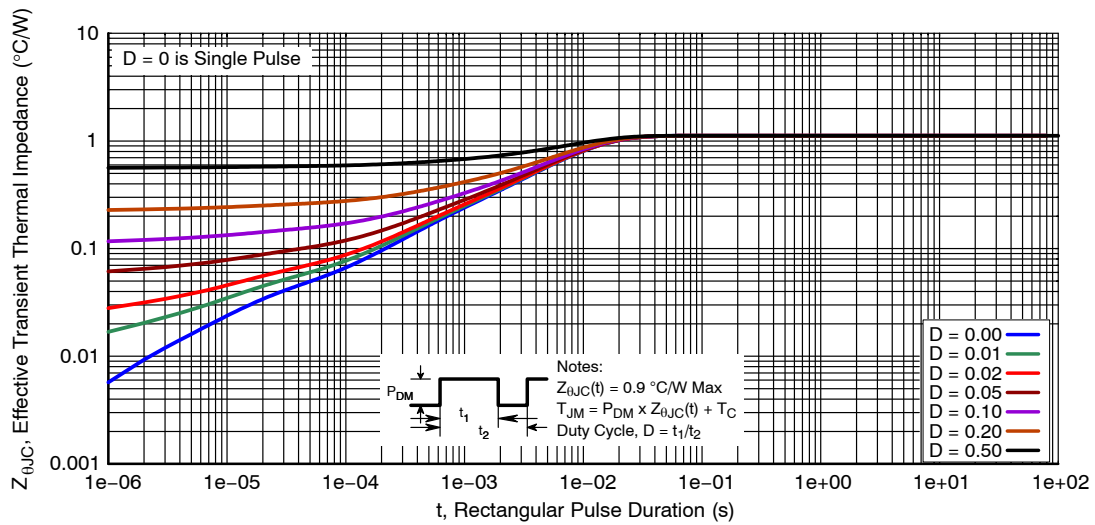


Figure 15. Transient Thermal Response

ORDERING INFORMATION

Device Order Number	Device Marking	Package Type	Shipping†
NTMFSC2D6N08XTWG	3X	DFN8 5x6 (Pb-Free/Halogen Free)	3000 / Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

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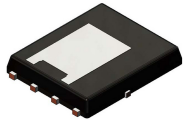
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REVISION HISTORY

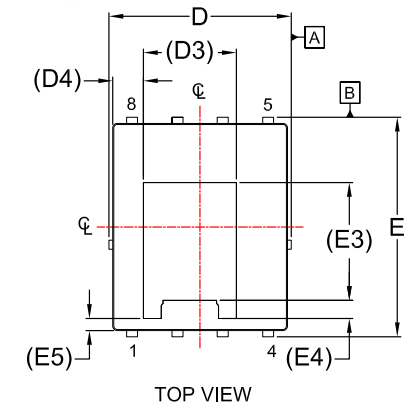
Revision	Description of Changes	Date
0	Initial production data sheet version release.	4/22/2025
1	Added Min and Max values for Charges, Capacitance, and Gate Resistance in the Electrical Characteristics table. + Rebrand to onsemi format	5/4/2026

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.

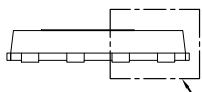



DFN8 5x6.15, 1.27P, DUAL COOL
CASE 506EG
ISSUE D

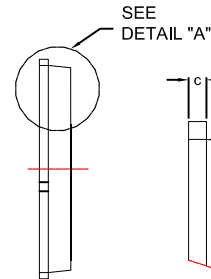
DATE 25 AUG 2020



TOP VIEW



FRONT VIEW

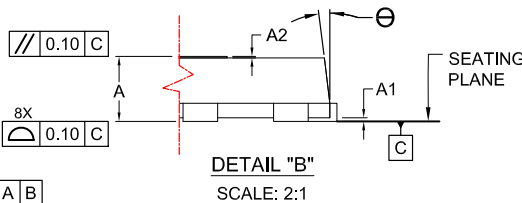
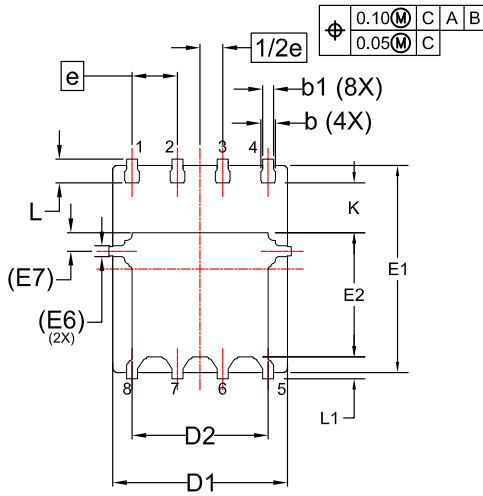


SIDE VIEW

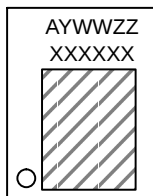
DETAIL "A"
SCALE: 2:1

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.
4. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
5. SEATING PLANE IS DEFINED BY THE TERMINALS. "A1" IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.


DETAIL "B"
SCALE: 2:1


BOTTOM VIEW

GENERIC
MARKING DIAGRAM*


XXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.85	0.90	0.95
A1	-	-	0.05
A2	-	-	0.05
b	0.31	0.41	0.51
b1	0.21	0.31	0.41
c	0.20	0.25	0.30
D	4.90	5.00	5.10
D1	4.80	4.90	5.00
D2	3.67	3.82	3.97
D3	2.60 REF		
D4	0.86 REF		
E	6.05	6.15	6.25
E1	5.70	5.80	5.90
E2	3.38	3.48	3.58
E3	3.30 REF		
E4	0.50 REF		
E5	0.34 REF		
E6	0.30 REF		
E7	0.52 REF		
e	1.27 BSC		
1/2e	0.635 BSC		
K	1.30	1.40	1.50
L	0.56	0.66	0.76
L1	0.52	0.62	0.72
Θ	0°	---	12°

LAND PATTERN
RECOMMENDATION
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SOLDERING AND MOUNTING TECHNIQUES
REFERENCE MANUAL, SOLDERRM/D.

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